## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:

a high-breakdown-voltage regulator configured to operate at a high input voltage, said regulator comprising resistors connected in series to divide a voltage output from a transistor connected to a power supply line, said transistor having a gate connected to a differential amplifier circuit receiving a first input from a first reference voltage generating circuit and a second input as a feedback voltage divided by said resistors;

a second reference voltage generating circuit structured as a low-breakdown-voltage component and configured to receive an output voltage from the high-breakdown-voltage regulator to generate a reference voltage;

a differential amplifier circuit structured as another low-breakdown-voltage component and configured to receive the output voltage from the high-breakdown-voltage regulator and the reference voltage from the reference voltage generating circuit to produce a drive voltage;

an output driver structured as a high-breakdown-voltage component and configured to ~~operated~~ operate based on the drive voltage, wherein the output driver is a MOS transistor;

~~a diode inserted between a gate and a source of the MOS transistor, the diode having a reverse breakdown voltage lower than an oxide breakdown voltage of the MOS transistor;~~

~~a constant current inverter inserted between a power supply line and the output driver;~~ and

resistors connected in series to the output driver to divide an output voltage of the output driver and feed the divided voltage back to the differential amplifier circuit.

2. (Original) The semiconductor device of claim 1, wherein the high-breakdown-voltage output driver and the low-breakdown-voltage components are MOS transistors with gate oxide films having a first thickness.

3. (Currently Amended) The semiconductor device of claim 2, wherein the high-breakdown-voltage regulator ~~is structured by~~ comprises a high-breakdown-voltage MOS transistor with a gate oxide film having a second thickness greater than the first thickness.

4. (Currently Amended) The semiconductor device of claim 1, wherein the output driver is a P-channel MOS transistor, the semiconductor device further comprising a ~~and the~~ diode inserted between the gate and the source of the P-channel MOS transistor [[has]] having a reverse breakdown voltage lower than an oxide breakdown voltage of the P-channel MOS transistor.

5. (Currently Amended) The semiconductor device of claim 1, wherein the output driver is an N-channel MOS transistor, the semiconductor device further comprising a ~~and the~~ diode [[is]] inserted between the gate and the source of the N-channel MOS transistor or between the gate and the ground and [[has]] having a reverse breakdown voltage lower than an oxide breakdown voltage of the N-channel MOS transistor.

6. (Currently Amended) The semiconductor device of claim 1, wherein the output driver is a P-channel MOS transistor, the semiconductor device further comprising a constant current inverter inserted between the differential amplifier circuit and the output driver, the constant current inverter comprising:

a constant current circuit connected between a power supply line and the output driver; and a MOS transistor controlled by the drive voltage output from the differential amplifier circuit.

7. (Currently Amended) The semiconductor device of claim 1, wherein the output driver is a P-channel MOS transistor, the semiconductor device further comprising a constant current inverter inserted between a power supply line and the output driver, the constant current inverter comprising:

a first N-channel MOS transistor to which the reference voltage generated by the reference voltage generator is supplied;

a first P-channel MOS transistor connected in series to the first N-channel MOS transistor to produce a constant current;

a second P-channel MOS transistor defining a constant current circuit under a current mirror configuration; and

a second N-channel MOS transistor to which the drive voltage output from the differential amplifier circuit is supplied.

8. (Currently Amended) A semiconductor device comprising:

a reference voltage generating circuit configured to generate a reference voltage, said circuit comprising resistors connected in series to divide a voltage output from a transistor connected to a power supply line, said transistor having a gate connected to a differential amplifier circuit receiving a first input from a reference voltage generating circuit and a second input as a feedback voltage divided by said resistors;

a differential amplifier circuit configured to receive the reference voltage and generate a drive voltage;

an output driver configured to operate based on the drive voltage, wherein the output driver is a MOS transistor;

a diode ~~inserted between~~ inserted between a gate and a source of the MOS transistor, the diode having a reverse breakdown voltage lower than an oxide breakdown voltage of the MOS transistor;

resistors connected in series to the output driver to divide an output voltage of the output driver and feed the divided voltage back to the differential amplifier circuit; and

a constant current circuit inserted between a power supply-line and a combination of the reference voltage generating circuit and the differential amplifier circuit.

9. (Original) The semiconductor device of claim 8, wherein the constant current circuit is structure by a depression-mode N-channel or P-channel MOS transistor.

10. (Original) The semiconductor device of claim 8, wherein the constant current circuit is structured by an enhancement-mode N-channel or P-channel MOS transistor.

11. (Currently Amended) The semiconductor device of claim 8, wherein the constant current circuit ~~is structure by~~ includes multiple MOS transistors connected in series to form a multi-stage constant current circuit.